



Correction to: Impact of film thickness on optical properties and optoelectrical parameters of novel CuGaGeSe₄ thin films synthesized by electron beam deposition

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Figure 2 has been published incorrectly in the original publication of the article. The correct version of the figure is provided with this correction.

The original article can be found online at <https://doi.org/10.1007/s11082-020-02448-9>.

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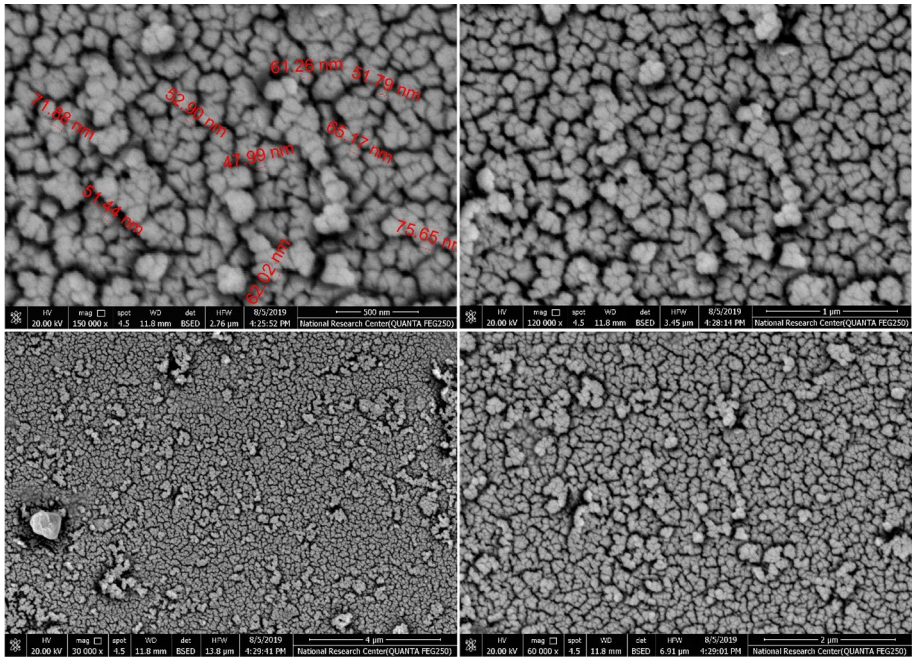


Fig. 2 The FE-SEM micrographs of the CuGaGeSe_4 thin films at different magnification powers, as depicted, the ternary CuGaGeSe_4 thin-film samples have a homogeneous surface and free crack samples

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